

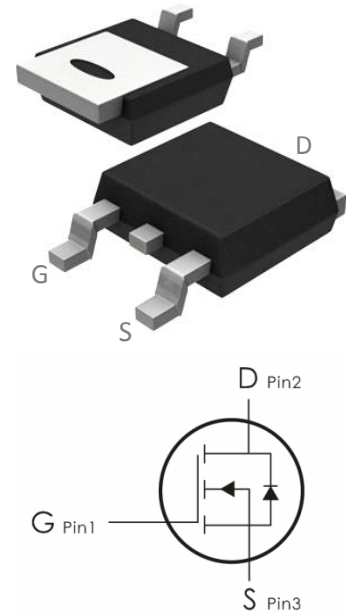
Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=30V, I_D=120A, R_{DS(on)} < 3.5 m\Omega @ V_{GS}=10V$ (Typ: $2.8 m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.
- 6) MSL3



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DOD4132	D4132	TO- 252	2500 pcs/Reel

Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_C=25^\circ C^1$	120	A
	Continuous Drain Current- $T_C=100^\circ C^1$	84	
	Pulsed Drain Current ²	360	
E_{AS}	Single Pulse Avalanche Energy ³	196	mJ
P_D	Power Dissipation, $T_C=25^\circ C$	73.5	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.7	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62	

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourtce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	30	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =30V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	1.2	1.5	2.5	V
R _{DS(ON)}	Drain-Source On Resistance ⁴	V _{GS} =10V, I _D =20A	---	2.8	3.5	m Ω
		V _{GS} =4.5V, I _D =10A	---	4.6	6	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	3100	---	pF
C _{Oss}	Output Capacitance		---	400	---	
C _{rss}	Reverse Transfer Capacitance		---	315	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} =15V, I _D =30A, V _{GS} =10V, R _{GEN} =3.3Ω	---	9	---	ns
t _r	Rise Time		---	19	---	ns
t _{d(off)}	Turn-Off Delay Time		---	58	---	ns
t _f	Fall Time		---	15.2	---	ns
Q _g	Total Gate Charge	V _{GS} =10 V, V _{DS} =15V, I _D =30A	---	30	---	nC
Q _{gs}	Gate-Source Charge		---	8.6	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	11.7	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Source-Drain Diode Forward Voltage	V _{GS} =0V, I _S =1A	---	---	1	V
I _S	Continuous Source Current	V _D =V _G =0V	---	---	120	A
I _{SM}	Pulsed Source Current		---	---	360	A
T _{rr}	Reverse Recovery Time	IF=30A , dI/dt=100A/μs , T _J =25°C	---	18	---	ns
q _{rr}	Reverse Recovery Charge		---	8	---	nC

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : $T_J=25^{\circ}C$, $V_{DD}=15V$, $V_G=10V$, $L=0.5mH$
4. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Characteristics: ($T_c=25^{\circ}C$ unless otherwise noted)

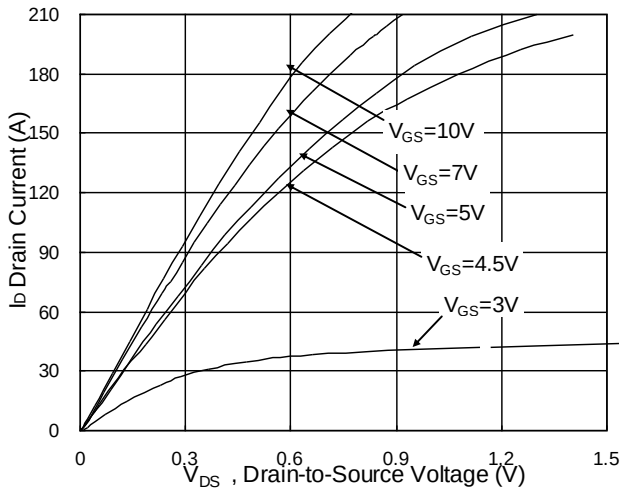


Fig.1 Typical Output Characteristics

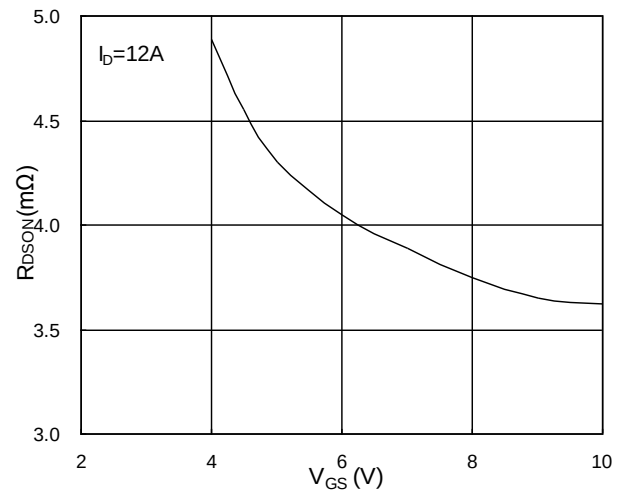


Fig.2 On-Resistance vs. G-S Voltage

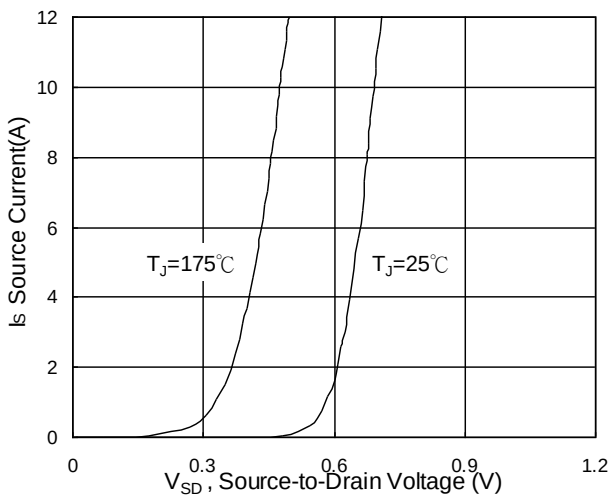


Fig.3 Forward Characteristics of Reverse

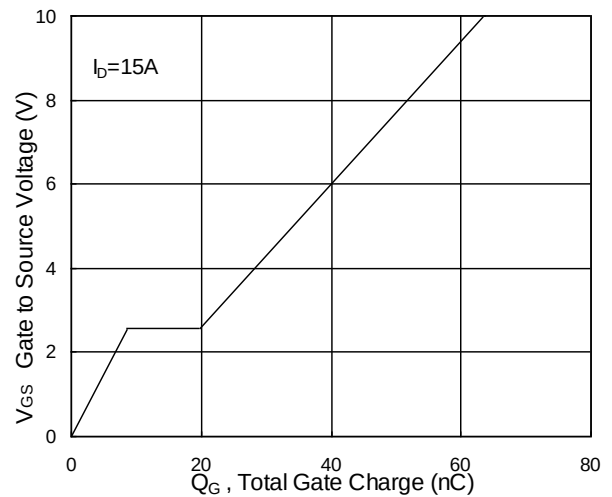


Fig.4 Gate-Charge Characteristics

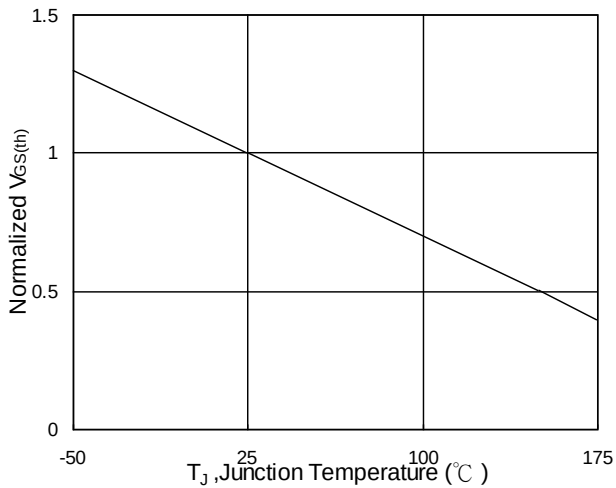


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

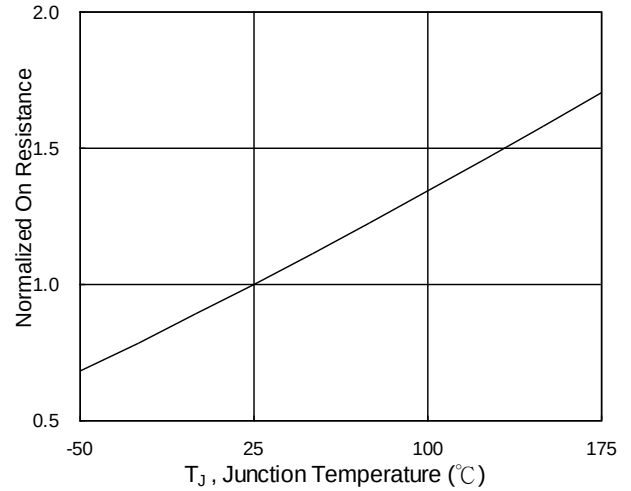


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

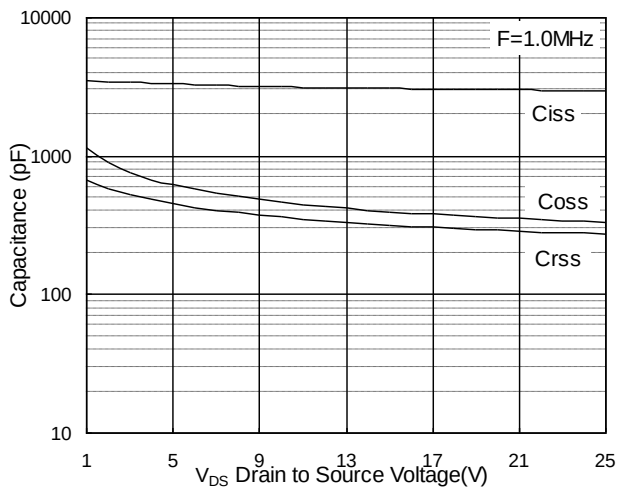


Fig.7 Capacitance

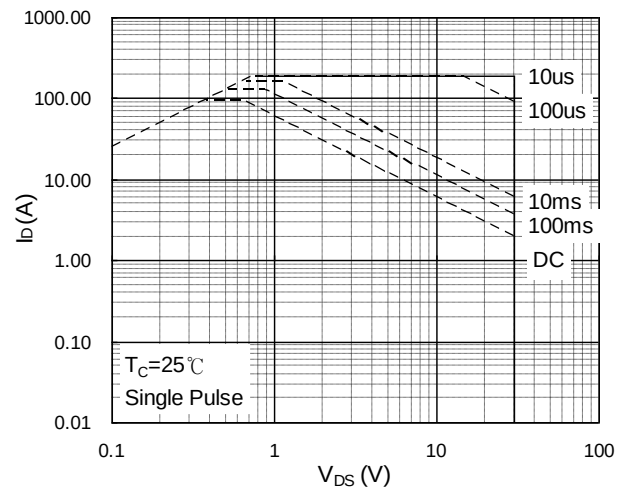


Fig.8 Safe Operating Area

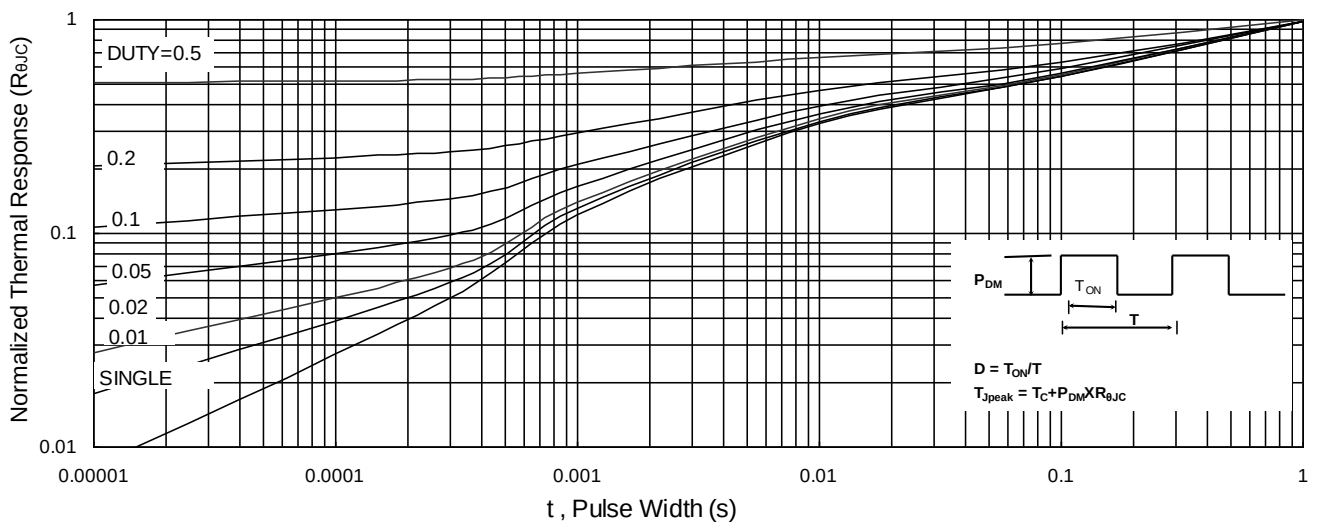


Fig.9 Normalized Maximum Transient Thermal Impedance

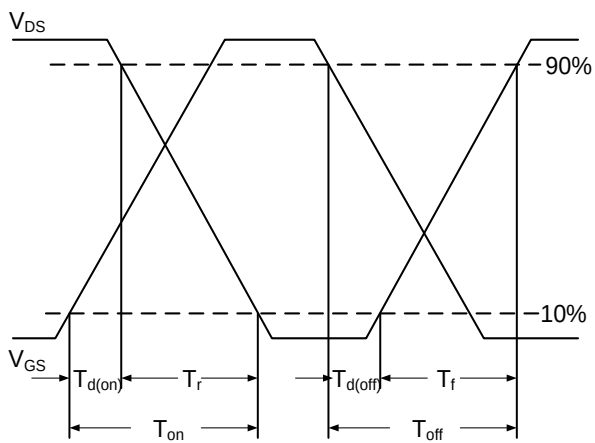


Fig.10 Switching Time Waveform

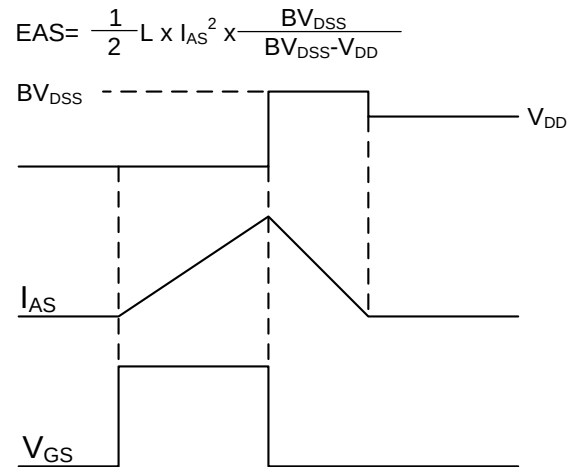


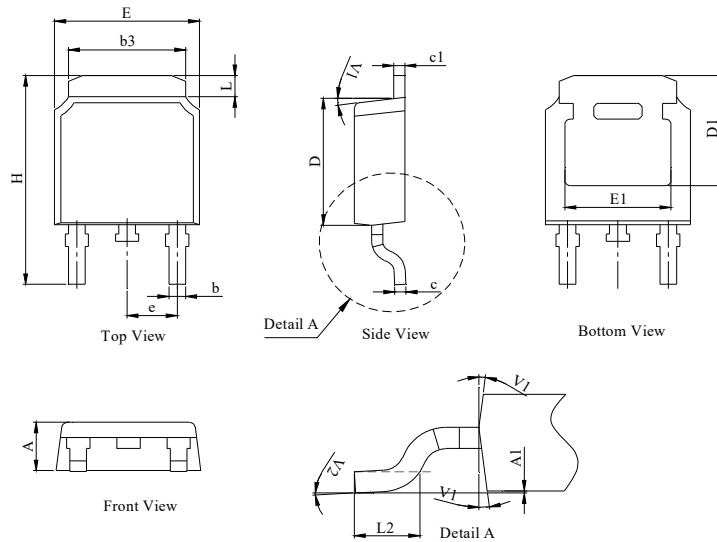
Fig.11 Unclamped Inductive Switching Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

TO-252 Package Information

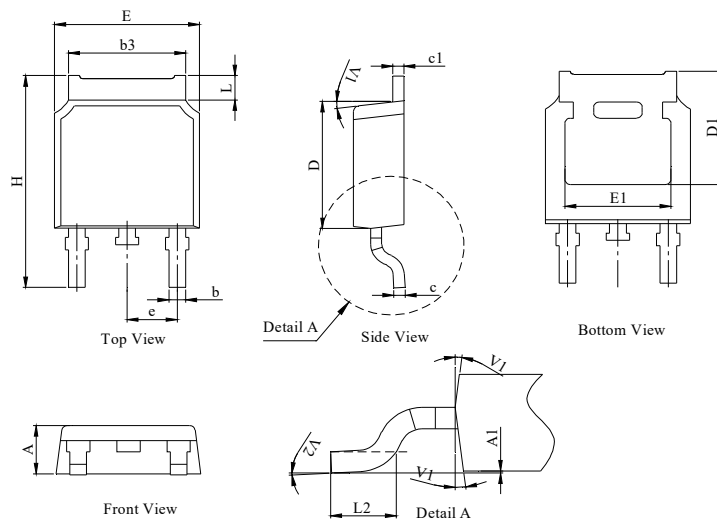
Package Outline Type-A

UNIT: mm



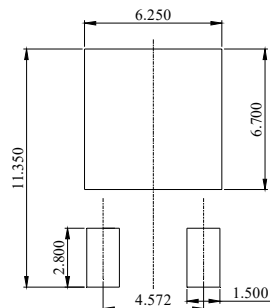
DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.18	2.30	2.39
A1	0	--	0.13
b	0.64	0.76	0.89
c	0.40	0.50	0.61
c1	0.46	0.50	0.58
D	5.97	6.10	6.23
D1	5.05	--	--
E	6.35	6.60	6.73
E1	4.32	--	--
b3	5.21	5.38	5.55
e	2.29 BSC		
H	9.40	10.00	10.40
L	0.89	--	1.27
L2	1.40	--	1.78
V1	7° REF		
V2	0°	--	6°

Package Outline Type-B



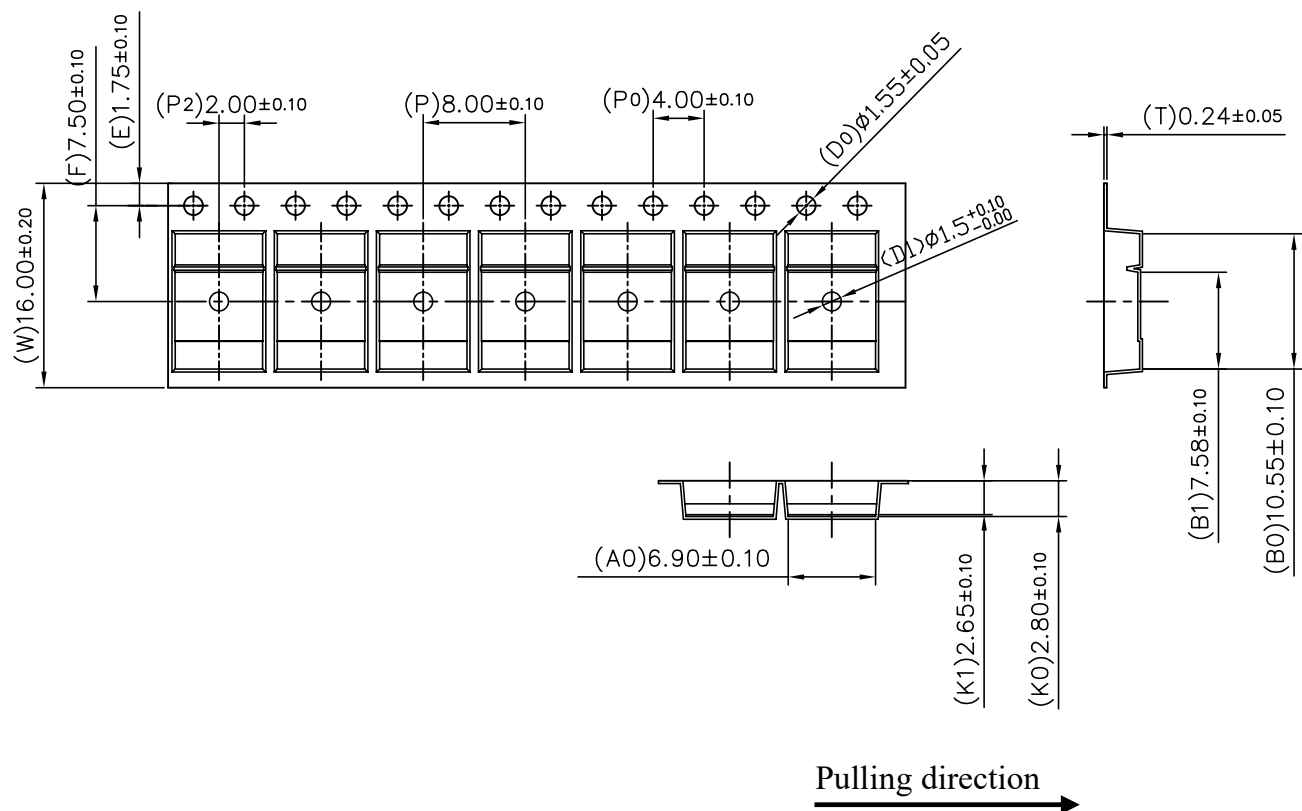
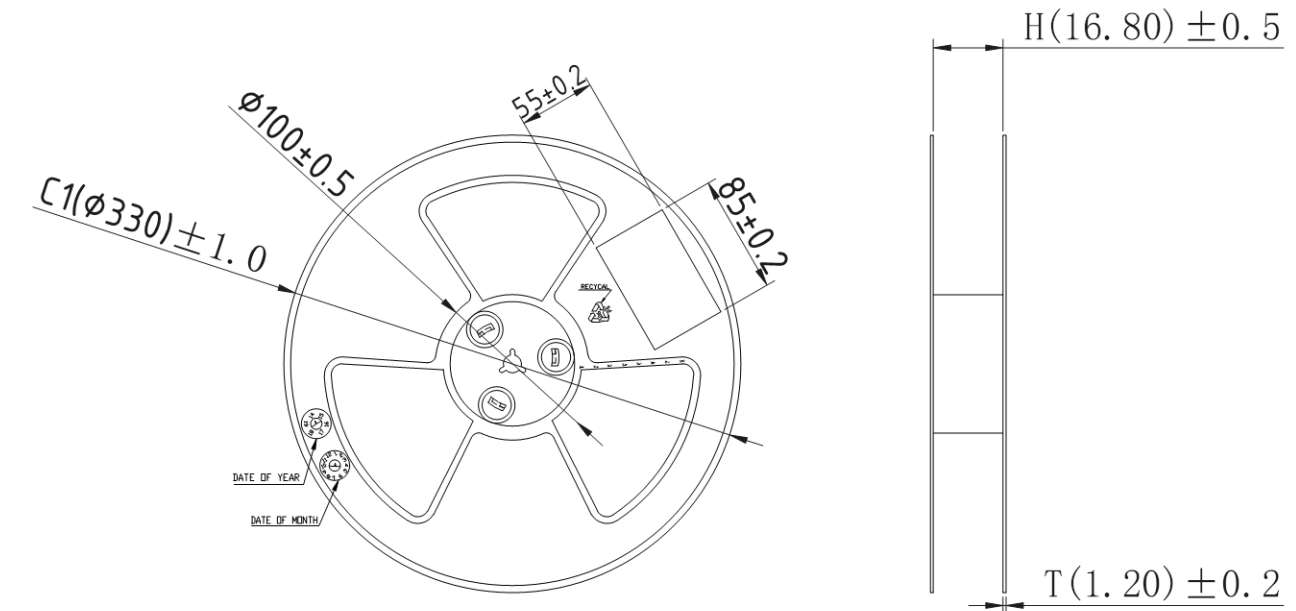
DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.10	2.30	2.40
A1	0	--	0.13
b	0.66	0.76	0.86
b3	5.21	5.38	5.55
c	0.40	0.50	0.60
c1	0.44	0.50	0.58
D	5.90	6.10	6.30
D1	5.30 REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.29 BSC		
H	9.50	10.00	10.70
L	1.09	--	1.21
L2	1.35	--	1.65
V1	7° REF		
V2	0°	--	6°

Recommended Soldering Footprint



Tape & Reel Information

Dimensions in mm



Package Information:

①. Doingter LOGO

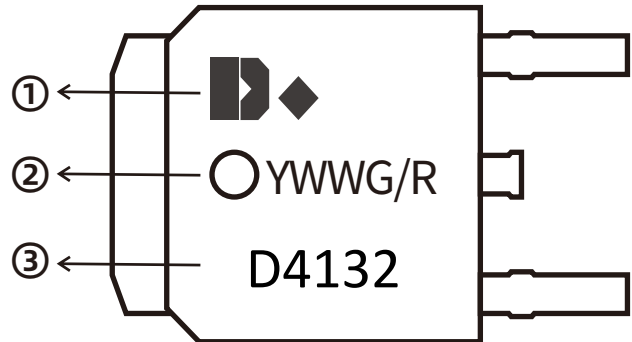
②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)

③ Part NO



Previous Version

Version	Date	Subjects (major changes since last revision)
1.2	2025-06-25	Release of final version

Attention :

- Information furnished in this document is believed to be accurate and reliable. However, Shenzhen Doingter Semiconductor Co.,Ltd. assumes noresponsibility for the consequences of use without consideration for such information nor use beyond it.
- Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Shenzhen Doingter complies with the agreement. Products and information provided in this document have no infringement of patents.
- Shenzhen Doingter assumes noresponsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.  Is a registered trademark of Shenzhen Doingter Semiconductor Co., Ltd. Copyright © 2013 Shenzhen DoingterSemiconductor Co.,Ltd. Printed All rights reserved.